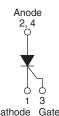
Vishay Semiconductors

Thyristor, Surface Mount, Phase Control SCR, 16 A



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D²PAK (TO-263AB)

Cathode Gate

PRIMARY CHARACTERISTICS							
I _{T(AV)}	16 A						
V _{DRM} /V _{RRM}	1200 V						
V _{TM}	1.25 V						
I _{GT}	45 mA						
TJ	-40 to +125 °C						
Package	D ² PAK (TO-263AB)						
Circuit configuration	Single SCR						

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 gualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- · Easy control peak current at charger power up to reduce passive / electromechanical components
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-25TTS12SLHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS					
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5						
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A					
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	16.5	25.0						

Note

• T_A = 55 °C, T_J = 125 °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I _{T(AV)}	Sinusoidal waveform	16	^				
I _{RMS}		25	A				
V _{RRM} /V _{DRM}		1200	V				
I _{TSM}		350	A				
V _T	16 A, T _J = 25 °C	1.25	V				
dV/dt		500	V/µs				
dl/dt		150	A/µs				
TJ		-40 to +125	°C				

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} / I _{DRM} , AT 125 °C mA						
VS-25TTS12SLHM3	1200	1200	10						

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RoHS COMPLIANT HALOGEN

FREE



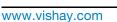
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ABSOLUTE MAXIMUM RATINGS									
PARAMETER	OVMDOL	SYMBOL TEST CONDITIONS		VAL	UES	UNITS			
PARAMETER	STNIDUL			TYP.	MAX.	UNITS			
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	1	6				
Maximum RMS on-state current	I _{RMS}			2	5	А			
Maximum peak, one-cycle,		10 ms sine pulse,	rated V _{RRM} applied	3	00	~			
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	3	50				
Maximum I ² t for fusing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	4	50	A ² s			
	1-1	10 ms sine pulse, no voltage reapplied			30				
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 10 m	6300		A²√s				
Maximum on-state voltage drop	V _{TM}	16 A, T _J = 25 °C		1.25		V			
On-state slope resistance	r _t	Т. _I = 125 °С		12.0		mΩ			
Threshold voltage	V _{T(TO)}	г(то) 1.0		.0	V				
Maximum reverse and direct leakage current	I/I	$T_J = 25 ^{\circ}C$ 0		.5					
Maximum reverse and direct leakage current	I _{RM} / I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	10		7			
Holding current	Ι _Η	VS-25TTS08, VS-25TTS12	resistive load initial I _T = 1 A		150	mA			
Maximum latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C			00				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$			00	V/µs			
Maximum rate of rise of turned-on current	di/dt								

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P _{GM}		8.0	W				
Maximum average gate power	P _{G(AV)}		2.0	vv				
Maximum peak positive gate current	+I _{GM}		1.5	А				
Maximum peak negative gate voltage	-V _{GM}		10	V				
		Anode supply = 6 V, resistive load, T_J = -10 °C	60	mA				
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	45					
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20					
		Anode supply = 6 V, resistive load, $T_J = -10 \ ^{\circ}C$	2.5					
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	2.0	V				
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	v				
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V rated value	0.25					
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA				

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T 105 %	4	μs				
Typical turn-off time	t _q	T _J = 125 °C	110					

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THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C				
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260					
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W				
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	C/W				
Approvimeto weight			2	g				
Approximate weight			0.07	oz.				
Marking device		Case style D ² PAK (TO-263AB)	25TTS	S12SH				

Note

(1) When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W

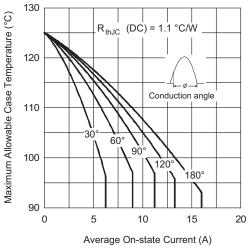
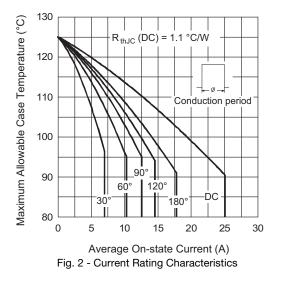


Fig. 1 - Current Rating Characteristics



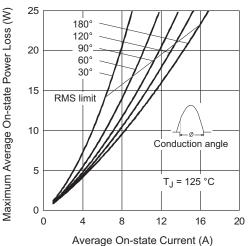
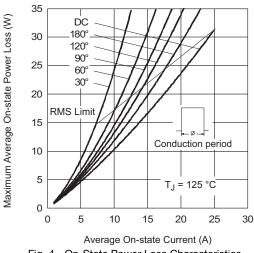


Fig. 3 - On-State Power Loss Characteristics





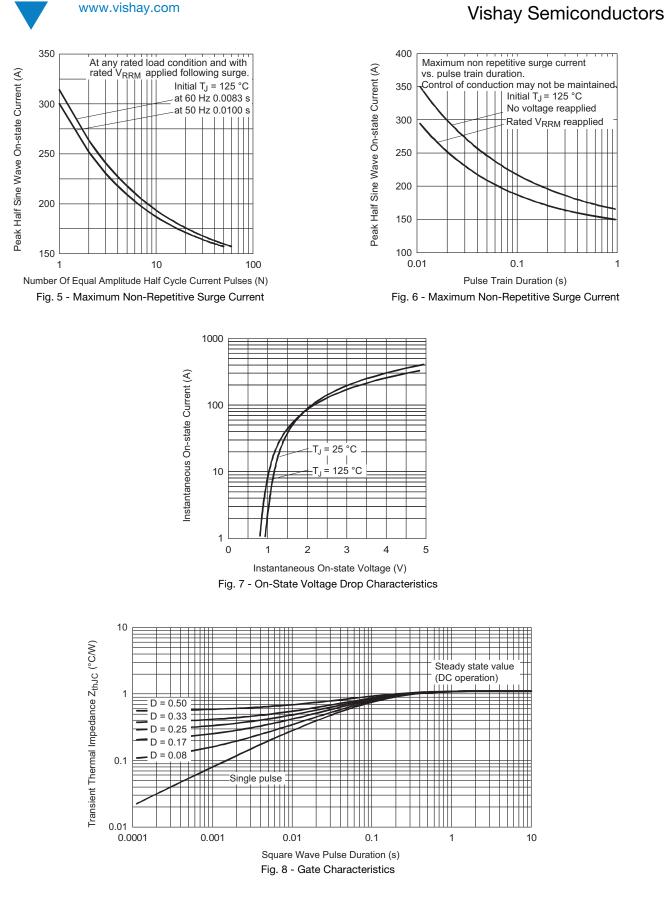
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VS-25TTS12SLHM3



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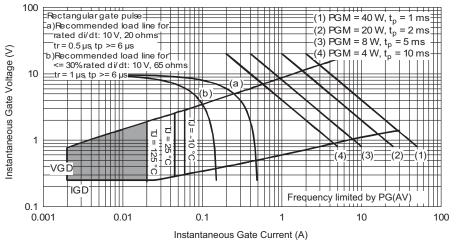


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

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SHA'

Device code	VS-	25	т	т	s	12	S	L	н	М3	
	1	2	3	4	5	6	(7)	8	9	10	
	1 - Vishay Semiconductors product										
	2 - Current rating (25 = 25 A)										
	3 -		Circuit configuration: T = single thyristor								
	4 -		Package: T = D ² PAK (TO-263AB)								
	5 -		e of silio standa	con: rd recov	ery rect	ifier					
	6 -	Vol	tage rati	ng: volta	age cod	e x 100	= V _{RRM}	1	12 = 1	200 V	
	7 -	S =	surface	mounta	able						
	8 -	L =	L = tape and reel (left oriented), for different orientation contact factory								
	9 -	H =	AEC-Q	101 qua	alified						
	10 -	M3	= halog	en-free,	RoHS-0	complia	nt, and	termina	tions lea	ad (Pb)-fr	

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-25TTS12SLHM3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96317					

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Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES		NOTES		MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3		
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3		
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3		
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC			
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625			
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110			
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3		
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070			
c2	1.14	1.65	0.045	0.065			L3	0.25 BSC		0.010 BSC				
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208			

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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